## 1 Characteristics

### Table 2. Absolute ratings (limiting values; $T_j = 25 \text{ °C}$ , unless otherwise specified)

Symbol	Parameter			Value	Unit
I <sub>T(RMS)</sub>	On-state rms current (full sine wave) $T_c = 97 \text{ °C}$			8	А
1	Non repetitive surge peak on-state current	F = 50 Hz	t <sub>p</sub> = 20 ms	60	А
<b>'</b> TSM	$I_{TSM}$ (full cycle, $T_j$ initial = 25 °C)		t <sub>p</sub> = 16.7 ms	63	A
l <sup>2</sup> t	I <sup>2</sup> t Value for fusing		t <sub>p</sub> = 10 ms	26	A <sup>2</sup> s
dl/dt	$ \begin{array}{ c c } \hline Critical rate of rise of on-state current I_G = 2 \ x \ I_{GT} \\ \hline t_r \leq 100 \ ns \end{array}  F = 60 \ Hz                                  $		T <sub>j</sub> = 125 °C	50	A/µs
V <sub>DSM</sub> , V <sub>RSM</sub>	Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms}$ $T_j$		T <sub>j</sub> = 25 °C	V <sub>DRM</sub> , V <sub>RRM</sub> + 100	V
I <sub>GM</sub>	Peak gate current $t_p = 20 \ \mu s$ $T_j = 125 \ ^{\circ}C$		4	А	
P <sub>G(AV)</sub>	Average gate power dissipation	1	W		
T <sub>stg</sub>	Storage junction temperature range			- 40 to + 150	°C
Тj	Operating junction temperature range			- 40 to + 125	°C



Symbol	Tost conditions	Quadrant		T8xxT			l lmit	
Symbol	Test conditions	Quadrant		T810T	T820T	T825T	T835T	Unit
I <sub>GT</sub> <sup>(1)</sup>	V = 12 V R = 20 O	-    -	MAX.	10	20	25	35	mA
'GT`´	$V_D = 12 V, R_L = 30 \Omega$	IV				40		
V <sub>GT</sub>	$V_D = V_{DRM}, R_L = 30 \Omega,$ $T_j = 25 \text{ °C}$	ALL	MAX.	X. 1.3			V	
V <sub>GD</sub>	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega,$ $T_j = 125 \text{ °C}$	ALL	MIN.	0.2			V	
I <sub>H</sub> <sup>(2)</sup>	I <sub>T</sub> = 500 mA	1	MAX.	15	25	30	40	mA
	I <sub>G</sub> = 1.2 I <sub>GT</sub>	I - III	MAX.	20	35	40	50	mA
ΙL		IV				40		
		II		25	40	70	70	
dV/dt <sup>(2)</sup>	$V_{D} = 67\% V_{DRM,}$ gate open	T <sub>j</sub> = 125 °C	– MIN.	100	750	500	2000	V/µs
uv/ut · ·		$T_j = 150 \ ^{\circ}C^{(3)}$		50	500	300	1000	
	(dV/dt)c = 0.1 V/µs			5.4				
	(dV/dt)c = 10 V/µs	T <sub>j</sub> = 125 °C		2		4.5		
(dI/dt)c <sup>(2)</sup>	Without snubber		MIN.		3.4		8	A/ms
	(dV/dt)c = 0.1 V/µs		IVIIIN.	2.5				AVIIIS
	(dV/dt)c = 10 V/µs	T <sub>j</sub> = 150 °C <sup>(3)</sup>		1		2		
	Without snubber	]			2		6.5	

Table 3. Electrical characteristics (T<sub>i</sub> = 25 °C, unless otherwise specified)

1. Minimum  $I_{GT}$  is guaranteed at 5% of  $I_{GT}$  max.

2. For both polarities of A2 referenced to A1.

3. Derating information for excess temperature above  ${\sf T}_j\,{\sf max}.$ 

#### **Table 4. Static characteristics**

Symbol	Test	Value	Unit		
V <sub>T</sub> <sup>(1)</sup>	I <sub>TM</sub> = 11.3 A, t <sub>p</sub> = 380 μs	T <sub>j</sub> = 25 °C	MAX.	1.60	V
V <sub>TO</sub> <sup>(1)</sup>	Threshold voltage	T <sub>j</sub> = 125 °C	MAX.	0.87	V
R <sub>D</sub> <sup>(1)</sup>	Dynamic resistance	T <sub>j</sub> = 125 °C	MAX.	60	mΩ
_	V <sub>DRM</sub> = V <sub>RRM</sub>	T <sub>j</sub> = 25 °C	MAX.	5	μA
I <sub>DRM</sub> , I <sub>RRM</sub>		T <sub>j</sub> = 125 °C	MAA.	1	
	$V_{D} = 0.9 \times V_{DRM}$	$T_j = 150 \ ^{\circ}C^{(2)}$	TYP.	1.9	mA

1. For both polarities of A2 referenced to A1.

2. Derating information for excess temperature above  ${\sf T}_j\,{\sf max}.$ 



Symbol	Parameter	Value	Unit			
R <sub>th(j-c)</sub>	Junction to case (AC)	2.8	°C/W			
R <sub>th(j-a)</sub>	Junction to ambient (DC)	60	°C/W			

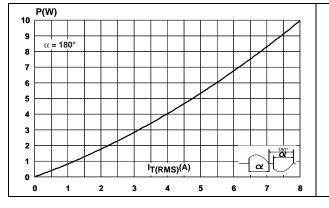
IT(RMS)(A)

10

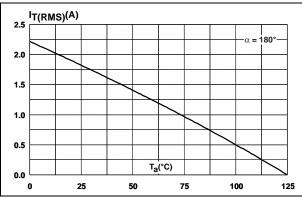
9

### Table 5. Thermal resistance

#### Figure 1. Maximum power dissipation versus rms on-state current



# Figure 3. On-state rms current versus ambient temperature (free air convection)





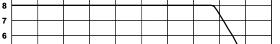


Figure 2. On-state rms current versus case

temperature

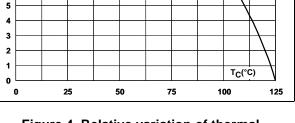


Figure 4. Relative variation of thermal impedance versus pulse duration

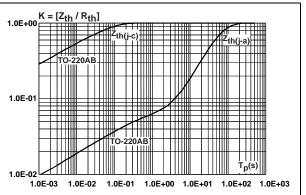
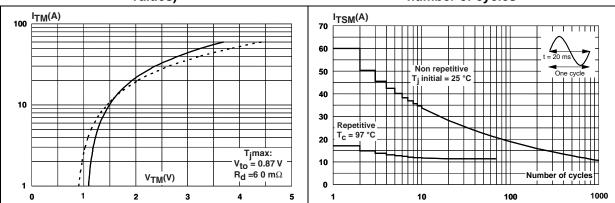


Figure 6. Surge peak on state current versus number of cycles

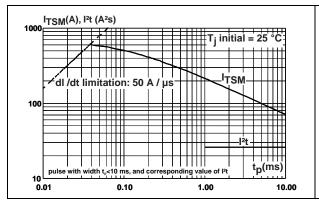


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α = 180°

# Figure 7. Non repetitive surge peak on-state current for a sinusoidal



#### Figure 9. Relative variation of holding current and latching current versus junction temperature

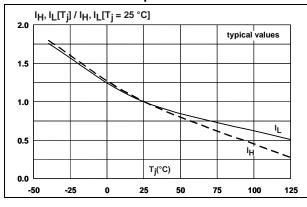
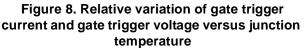


Figure 11. Relative variation of critical rate of decrease of main current versus junction temperature



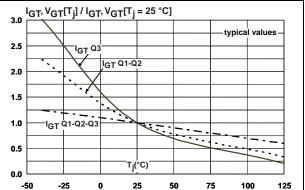


Figure 10. Relative variation of static dV/dt immunity versus junction temperature

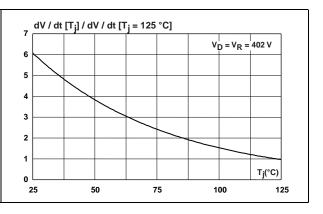
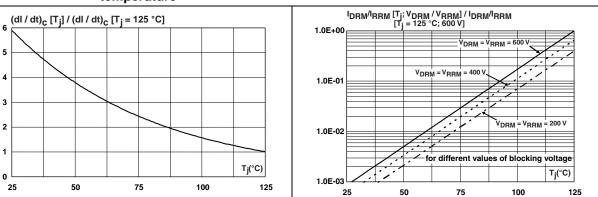


Figure 12. Relative variation of leakage current versus junction temperature





### 2 Package information

- Epoxy meets UL94, V0
- Lead-free packages

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK<sup>®</sup> is an ST trademark.

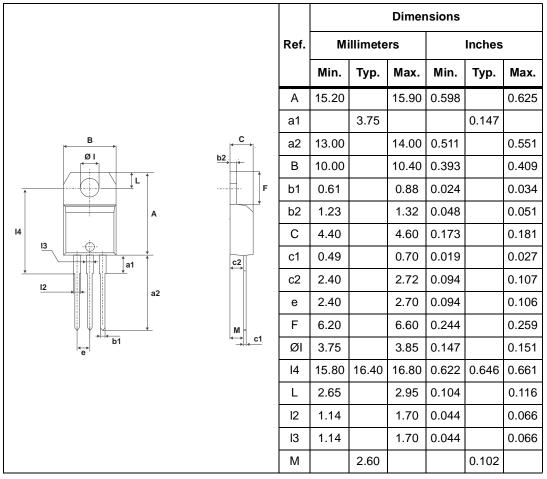


Table 6. TO-220AB Insulated dimensions



## 3 Ordering information

Figure 13. Ordering	information scheme
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	T	8 	10 	T	-	6 
TRIAC						
Current						
8 = 8 A						
Sensitivity						
10 = 10 mA						
20 = 20 mA						
25 = 25 mA						
35 = 35 mA						
Application specific						
Voltage						
6 = 600 V						_
Package						
I = TO-220AB-Ins.						

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T810T-6I	T810T-6I				
T820T-6I	T820T-6I	TO-220AB-Ins.	229	50	Tube
T825T-6I	T825T-6I	10-220AB-1115.	2.3 g	50	Tube
T835T-6I	T835T-6I				

## 4 Revision history

#### Table 8. Document revision history

Date	Revision	Changes
10-Sep-2009	1	First issue.
18-Jan-2010	2	Updated pag.1.
20-Sep-2011	3	Updated: <i>Features</i> . Replaced order codes with part numbers in <i>Table 1</i> .
16-Sep-2013	4	Replaced order codes with part numbers in <i>Table 1</i> .



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